

N-Channel 80 V (D-S) Super Junction Power MOSFET

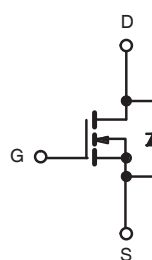
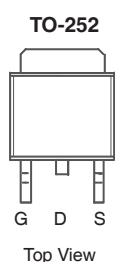
| PRODUCT SUMMARY | | | |
|-------------------|----------------------------|------------------------|--------------|
| $V_{(BR)DSS}$ (V) | $r_{DS(on)}$ (Ω) | I_D (A) ^c | Q_g (Typ.) |
| 80 | 0.0029 at $V_{GS} = 10$ V | 140 | 90 nC |
| | 0.0042 at $V_{GS} = 4.5$ V | 90 | |

FEATURES

- TrenchFET II Power MOSFET
- 100 % R_g and UIS Tested



RoHS
COMPLIANT



N-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted) | | | | |
|---|----------------|----------------|-----------------|------|
| Parameter | | Symbol | Limit | Unit |
| Gate-Source Voltage | | V_{GS} | ± 20 | V |
| Continuous Drain Current ($T_J = 175$ °C) ^b | $T_C = 25$ °C | I_D | 140 | A |
| | $T_C = 100$ °C | | 90 ^a | |
| Pulsed Drain Current | | I_{DM} | 560 | |
| Continuous Source Current (Diode Conduction) | | I_S | 135 | |
| Avalanche Current | | I_{AS} | 140 | |
| Single Avalanche Energy (Duty Cycle ≤ 1 %) | $L = 0.1$ mH | E_{AS} | 300 | mJ |
| Maximum Power Dissipation | $T_C = 25$ °C | P_D | 425 | W |
| | $T_C = 125$ °C | | 150 | |
| Operating Junction and Storage Temperature Range | | T_J, T_{stg} | - 55 to 175 | °C |

| THERMAL RESISTANCE RATINGS | | | | | |
|--|-----------------|------------|---------|---------|------|
| Parameter | | Symbol | Typical | Maximum | Unit |
| Maximum Junction-to-Ambient ^a | $t \leq 10$ sec | R_{thJA} | 10 | 15 | °C/W |
| | Steady State | | 20 | 35 | |
| Maximum Junction-to-Case | | R_{thJC} | 0.75 | 1.0 | |

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c. $t \leq 10$ s.

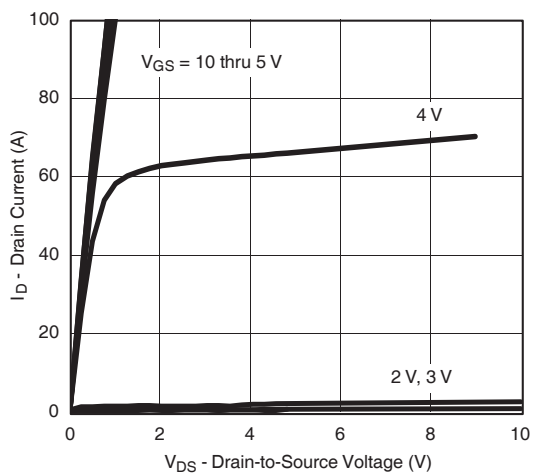
| SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | |
|--|--------------|--|------|-------------------|-----------|---------------|
| Parameter | Symbol | Test Conditions | Min. | Typ. ^a | Max. | Unit |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | 80 | | | V |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | 1 | | 3 | |
| Gate-Body Leakage | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 64\text{ V}, V_{GS} = 0\text{ V}$ | | | 1 | μA |
| | | $V_{DS} = 64\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$ | | | 10 | |
| | | $V_{DS} = 64\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$ | | | 150 | |
| On-State Drain Current ^b | $I_{D(on)}$ | $V_{DS} = 10\text{ V}, V_{GS} = 10\text{ V}$ | 140 | | | A |
| Drain-Source On-State Resistance ^b | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}, I_D = 30\text{ A}$ | | 0.0029 | 0.0035 | Ω |
| | | $V_{GS} = 10\text{ V}, I_D = 20\text{ A}, T_J = 125\text{ }^\circ\text{C}$ | | 0.0034 | 0.0040 | |
| | | $V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$ | | 0.0042 | 0.0055 | |
| Forward Transconductance ^b | g_{fs} | $V_{DS} = 64\text{ V}, I_D = 30\text{ A}$ | | 85 | | S |
| Dynamic | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0\text{ V}, V_{DS} = 64\text{ V}, f = 1\text{ MHz}$ | | 10050 | | pF |
| Output Capacitance | C_{oss} | | | 3340 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 460 | | |
| Total Gate Charge ^c | Q_g | $V_{DS} = 64\text{ V}, V_{GS} = 10\text{ V}, I_D = 30\text{ A}$ | | 98 | 120 | nC |
| Gate-Source Charge ^c | Q_{gs} | | | 20 | | |
| Gate-Drain Charge ^c | Q_{gd} | | | 30 | | |
| Turn-On Delay Time ^c | $t_{d(on)}$ | $V_{DD} = 64\text{ V}, R_L = 0.6\text{ }\Omega$ $I_D \cong 30\text{ A}, V_{GEN} = 10\text{ V}, R_g = 2.5\text{ }\Omega$ | | 10 | 20 | ns |
| Rise Time ^c | t_r | | | 18 | 25 | |
| Turn-Off Delay Time ^c | $t_{d(off)}$ | | | 55 | 80 | |
| Fall Time ^c | t_f | | | 15 | 22 | |
| Source-Drain Diode Ratings and Characteristics ($T_C = 25\text{ }^\circ\text{C}$) | | | | | | |
| Pulsed Current | I_{SM} | | | | 560 | A |
| Diode Forward Voltage | V_{SD} | $I_F = 20\text{ A}, V_{GS} = 0\text{ V}$ | | 0.8 | 1.5 | V |
| Reverse Recovery Time | t_{rr} | $I_F = 30\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$ | | 125 | 196 | ns |

Notes:

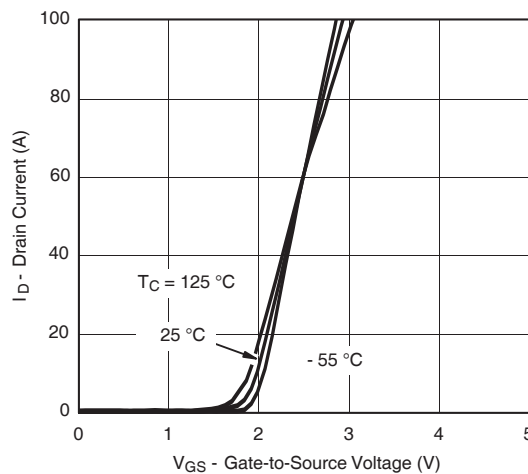
- For design aid only; not subject to production testing.
- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

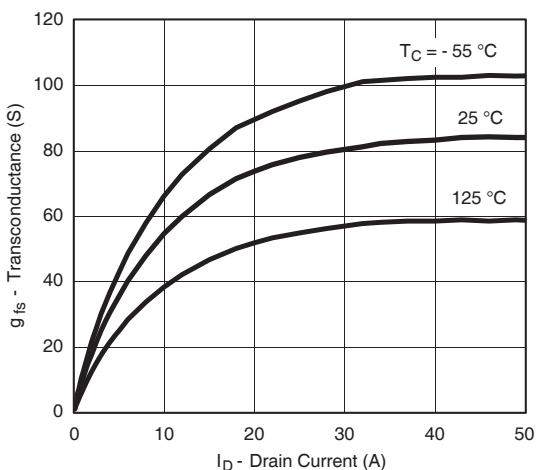
TYPICAL CHARACTERISTICS (25 °C unless noted)



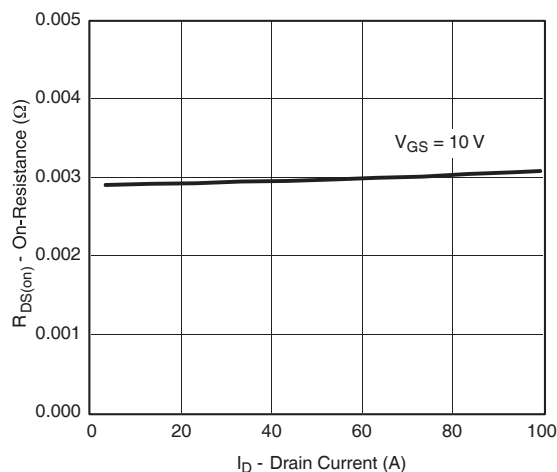
Output Characteristics



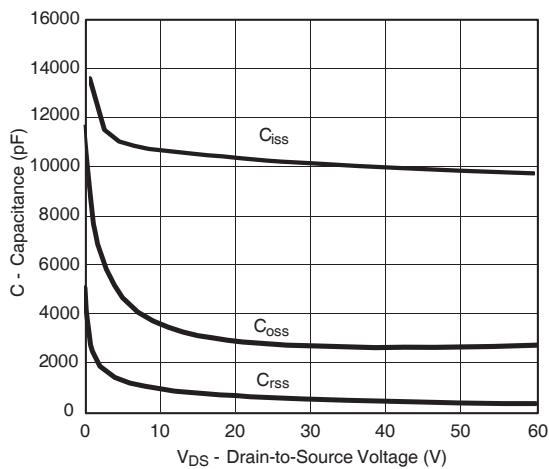
Transfer Characteristics



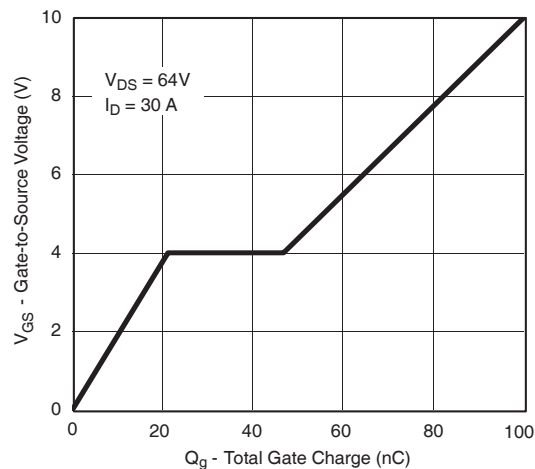
Transconductance



On-Resistance vs. Drain Current

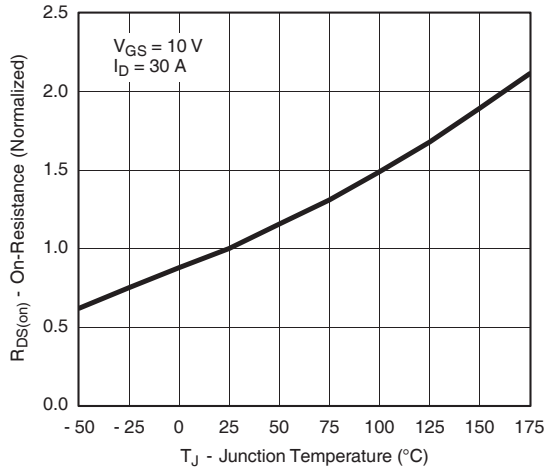


Capacitance

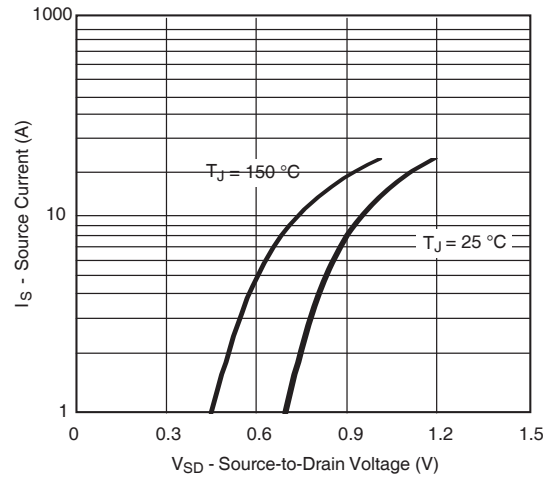


Gate Charge

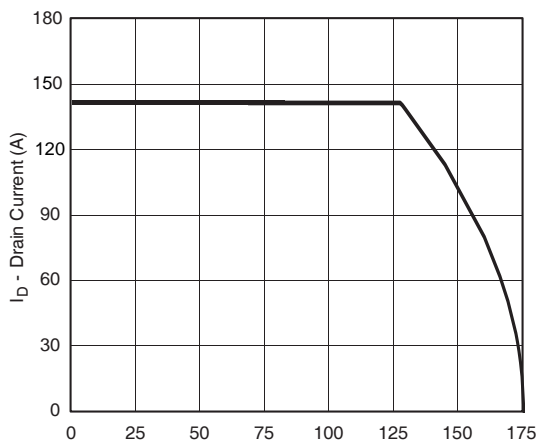
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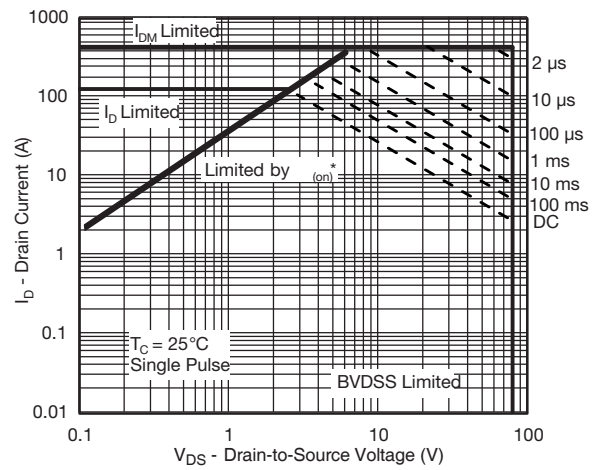
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



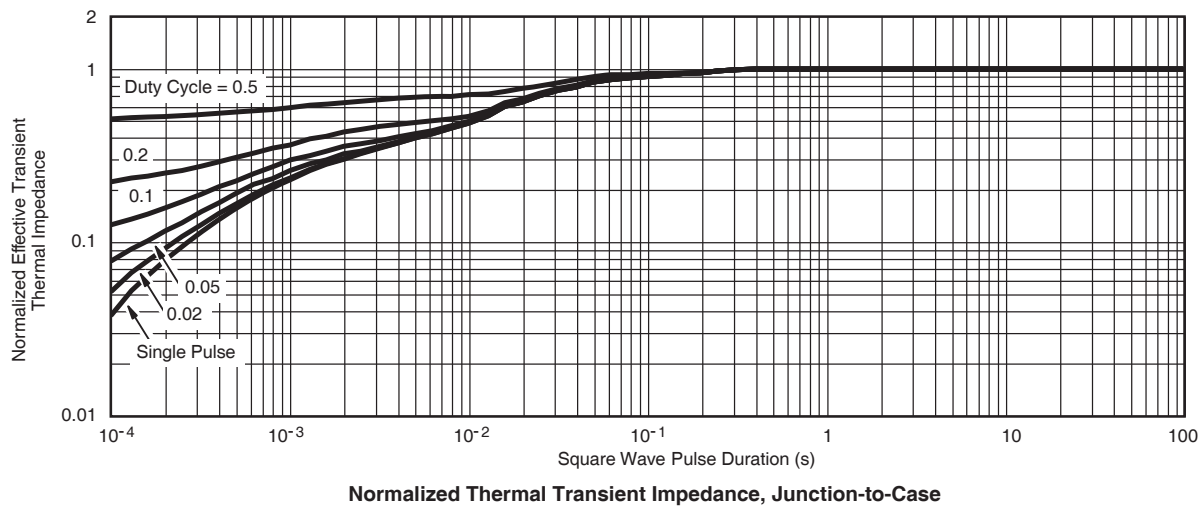
Maximum Drain Current vs. Ambient Temperature



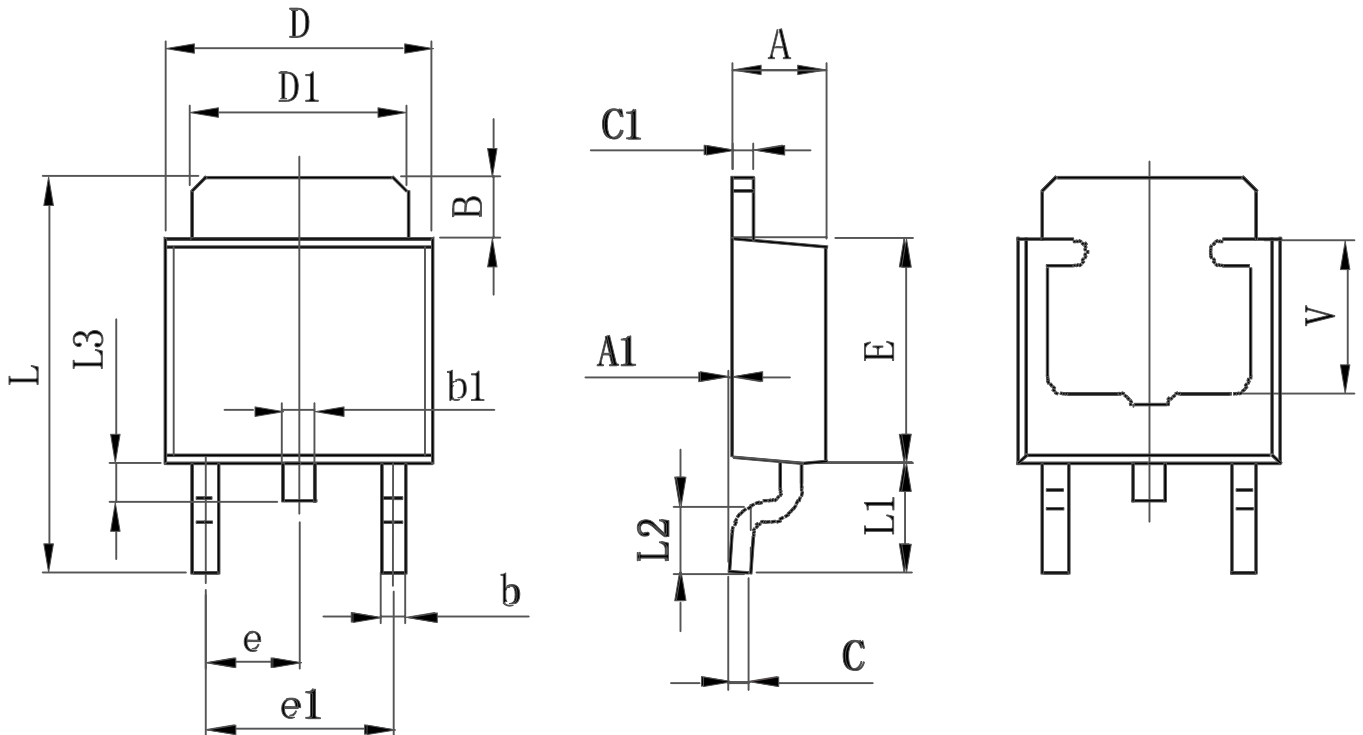
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

THERMAL RATINGS

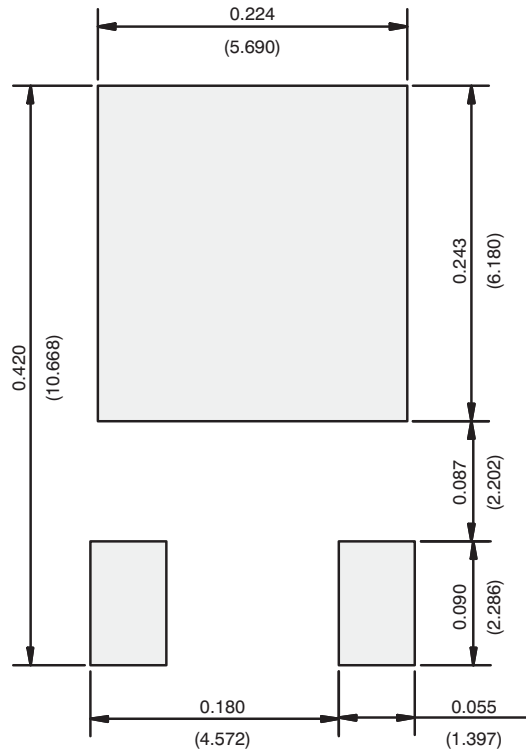


TO-252-2L PACKAGE OUTLINE DIMENSIONS



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 2.200 | 2.400 | 0.087 | 0.094 |
| A1 | 0.000 | 0.127 | 0.000 | 0.005 |
| B | 1.350 | 1.650 | 0.053 | 0.065 |
| b | 0.500 | 0.700 | 0.020 | 0.028 |
| b1 | 0.700 | 0.900 | 0.028 | 0.035 |
| c | 0.430 | 0.580 | 0.017 | 0.023 |
| c1 | 0.430 | 0.580 | 0.017 | 0.023 |
| D | 6.350 | 6.650 | 0.250 | 0.262 |
| D1 | 5.200 | 5.400 | 0.205 | 0.213 |
| E | 5.400 | 5.700 | 0.213 | 0.224 |
| e | 2.300 TYP. | | 0.091 TYP. | |
| e1 | 4.500 | 4.700 | 0.177 | 0.185 |
| L | 9.500 | 9.900 | 0.374 | 0.390 |
| L1 | 2.550 | 2.900 | 0.100 | 0.114 |
| L2 | 1.400 | 1.780 | 0.055 | 0.070 |
| L3 | 0.600 | 0.900 | 0.024 | 0.035 |
| V | 3.800 REF. | | 0.150 REF. | |

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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